	(Test Item)	(Condition)	(Reference)	(Time)
1	Pre-conditioning	Performed on surface mount devices (SMDs) prior to TC,AC, H3TRB & IOL/PTC stresses only.	JESD22-A113	1.Temperature Cycling:-40 ~60 5cycles 2.Bake:125 ,24H 3.Moisture Soak:85±2 85±5%/168h 4.Reflow*3cycles:260 ,3cycles time 5-60min
2	High Temperature Reverse Bias	Tjmax,100%VR	JESD22-A108	1000Hrs
3	Intermittent Operational Life	Tj 100 ,2min ON/2min OFF	MIL-STD-750 Method 1037	15000Cycles
4	(High-temperature High-humidity Reverse Bias)	85±2 85%±5%RH 80%VR Max=100V)	JESD22-A101	1000Hrs
4 alt	(Highly Accelerated Stress Test)	130±2 85%±5%RH,OR 110±2 85%±5%RH 80%VR Max=42V)	JESD22-A110	96Hrs OR 264Hrs
5	High-temperature High-humidity storage test	85±2 85±5%RH	MIL-STD-202F METHOD-103B	1000Hrs
5-1	DPA	After H3TRB,Visual Inspection,X-RAY,De-cap for Weld,De-cap for Die	NA	H3TRB 48H
6	Temperature Cycling	150 +15 -0 /15min, -55 +0 -10 /15min	JESD22-A104	1000 cycles
6-1	DPA	After TC,Visual Inspection,X-RAY,De-cap for Weld,De-cap for Die	NA	TC 48H
7	(High Temperature Storage)	150 +10 -0	JESD22-A103	1000Hrs
8	Low Temperature storage)	-55	Specification	1000H
9	Auto-clave	121 ±2 ,15 psig,100%RH	JESD22-A102	96Hrs
10	Solderability	235 ±5	J-STD-002	3
11	(Resistance to solder heat)	DIP 270±5 SMD: 260 (+5,-0)	JESD22-B106 JESD22-A111	DIP 7 (+2, -0) SMD :10'
12	(Bending Strength)	φ0.6mm~0.78mm W=0.5Kg 90±5° φ1.20mm W=2Kg	MIL-STD-750 Method 2036	3Times
13	(Terminal Strength)	φ0.6mm~φ0.78mm W=1Kg φ1.20mm W=3Kg	MIL-STD-750 Method 2036	15'
14	(Forward Surge Test	8.3ms,Single,Half-Wave	MIL-STD-750 Method 4066	5Times
15	Salt Spray Test	35±2 , 5±0.1% PH 6.5-7.2 1~2ml/80cm².h	GB/T 2423.17-2008	24H
16	(ESD)	HBM 100pF,1500Ω ,GPP:4KV; Others:2KV;	AEC-Q101-001/002	1cycle
17	Gate High Temperature Gate Bias	Tjmax,100%Vgs	JESD22-A108	1000Hrs